



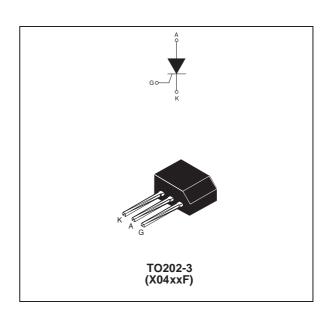
SENSITIVE 4A SCRS

### **MAIN FEATURES:**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	4	А
V <sub>DRM</sub> /V <sub>RRM</sub>	600 and 800	V
I <sub>GT</sub>	50 to 200	μΑ

### **DESCRIPTION**

Thanks to highly sensitive triggering levels, the X04 SCR series is suitable for all applications where the available gate current is limited, such as capacitive discharge ignitions, motor control in kitchen aids, overvoltage crowbar protection in low power supplies...



### **ABSOLUTE RATINGS** (limiting values)

Symbol	Param	Value	Unit		
I <sub>T(RMS)</sub>	RMS on-state current (180° conduction angle) $TI = 60^{\circ}C$ $Tamb = 25^{\circ}C$		TI = 60°C	4	А
			1.35		
IT <sub>(AV)</sub>	Average on-state current (180° conduction angle)		TI = 60°C	2.5	Α
		Tamb = 25°C	0.9		
I <sub>TSM</sub>	Non repetitive surge peak on-state	tp = 8.3 ms	Tj = 25°C	33	Α
	current		1) = 25 0	30	
l <sup>2</sup> t	I <sup>2</sup> t Value for fusing	tp = 10 ms	Tj = 25°C	4.5	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $tr \le 100$ ns	F = 60 Hz	Tj = 125°C	50	A/µs
I <sub>GM</sub>	Peak gate current	tp = 20 μs	Tj = 125°C	1.2	Α
P <sub>G(AV)</sub>	Average gate power dissipation Tj = 125°0		Tj = 125°C	0.2	W
T <sub>stg</sub> Tj	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

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## X04 Series

# **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise specified)

Symbol	Test Conditions			X04xx		Unit
				02	05	1
I <sub>GT</sub>			MIN.	_	20	μΑ
	$V_D = 12 \text{ V}$ $R_L = 140 \Omega$		MAX.	200	50	μ/,
V <sub>GT</sub>			MAX.	0	.8	V
$V_{\sf GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $R_{GK} = 1 \text{ k}\Omega$ $Tj = 125 ^{\circ}\text{C}$		MIN.	0.1		V
$V_{RG}$	I <sub>RG</sub> = 10 μA		MIN.	8		V
Ι <sub>Η</sub>	$I_T = 50$ mA $R_{GK} = 1$ k $\Omega$		MAX.	5		mA
ΙL	$I_G = 1 \text{mA}$ $R_{GK} = 1 \text{k}\Omega$		MIN.	6		mA
dV/dt	$V_D = 67\% V_{DRM} R_{GK} = 1k\Omega$	Tj = 110°C	MIN.	10	15	V/µs
$V_{TM}$	I <sub>TM</sub> = 8 A tp = 380 μs	Tj = 25°C	MAX.	1.	.8	V
V <sub>t0</sub>	Threshold voltage	Tj = 125°C	MAX.	0.95		V
R <sub>d</sub>	Dynamic resistance	Tj = 125°C	MAX.	100		mΩ
I <sub>DRM</sub>	V	Tj = 25°C	MAX.	Ę	5	μA
$I_{RRM}$	$V_{DRM} = V_{RRM}$ $R_{GK} = 1 \text{ k}\Omega$	Tj = 125°C		1	I	mA

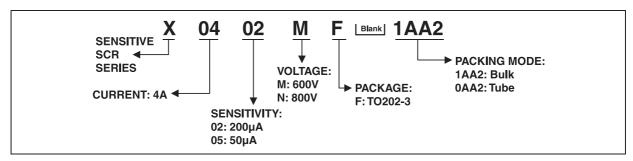
### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-l)</sub>	Junction to leads (DC)	15	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	100	

### PRODUCT SELECTOR

Part Number	Voltage		Sensitivity	Package	
	600 V	800 V			
X0402MF	Х		200 μΑ	TO202-3	
X0402NF		Х	200 μΑ	TO202-3	
X0405MF	X		50 μA	TO202-3	
X0405NF		X	50 μΑ	TO202-3	

### ORDERING INFORMATION

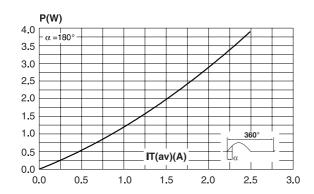


### **OTHER INFORMATION**

Part Number	Marking	Weight	Base Quantity	Packing mode
X04xxyF 1AA2	X04xxyF	0.8 g	250	Bulk
X04xxyF 0AA2	X04xxyF	0.8 g	50	Tube

**Note**: xx = sensitivity, y = voltage

**Fig. 1:** Maximum average power dissipation versus average on-state current.



**Fig. 2-2:** Average and D.C. on-state current versus ambient temperature (device mounted on FR4 with recommended pad layout).

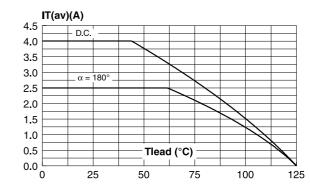
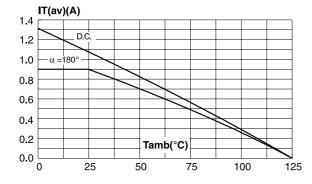
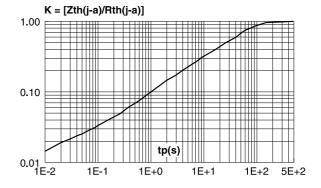


Fig. 2-1: Average and D.C. on-state current

versus lead temperature.

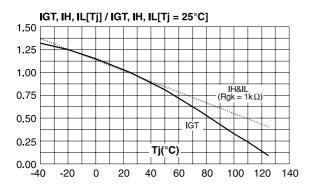
**Fig. 3:** Relative variation of thermal impedance junction to ambient versus pulse duration.



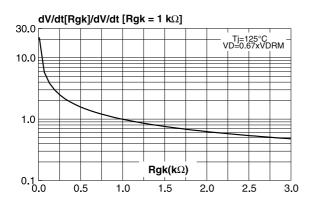


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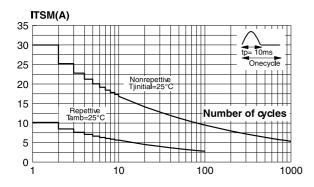
**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



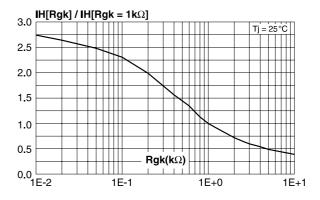
**Fig. 6:** Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).



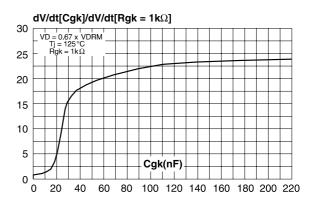
**Fig. 8:** Surge peak on-state current versus number of cycles.



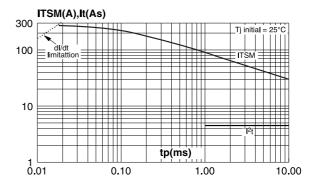
**Fig. 5:** Relative variation of holding current versus gate-cathode resistance (typical values).



**Fig. 7:** Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values).

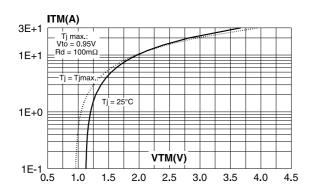


**Fig. 9:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms, and corresponding value of  $l^2t$ .



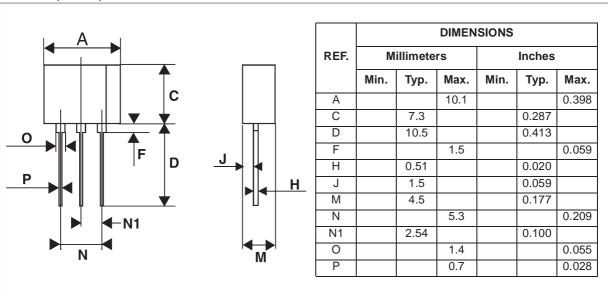
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**Fig. 10:** On-state characteristics (maximum values).



### **PACKAGE MECHANICAL DATA**

TO202-3 (Plastic)



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